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APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/828,067	04/06/2001		Don E. Curry	005040/TCG/PMD/LE	7268	
32588	7590	06/03/2005		EXAM	EXAMINER	
APPLIED 1 2881 SCOT		•	ZERVIGON, RUDY			
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Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	09/828,067	CURRY ET AL.	
Office Action Summary	Examiner	Art Unit	
	Rudy Zervigon	1763	
The MAILING DATE of this communication Period for Reply	n appears on the cover sheet v	vith the correspondence address	5
A SHORTENED STATUTORY PERIOD FOR FOR THE MAILING DATE OF THIS COMMUNICATION of time may be available under the provisions of 37 Contents after SIX (6) MONTHS from the mailing date of this communication of the period for reply specified above is less than thirty (30) days of the period for reply is specified above, the maximum statutory failure to reply within the set or extended period for reply will, by Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	ON. FR 1.136(a). In no event, however, may a on. , a reply within the statutory minimum of th period will apply and will expire SIX (6) MO statute, cause the application to become A	reply be timely filed rty (30) days will be considered timely. NTHS from the mailing date of this commun BANDONED (35 U.S.C. § 133).	nication.
Status			
1) ☐ Responsive to communication(s) filed on 2a) ☐ This action is FINAL . 2b) ☐ 3) ☐ Since this application is in condition for a closed in accordance with the practice un	This action is non-final.	·	rits is
Disposition of Claims			
4) Claim(s) 21-35 and 38-41 is/are pending 4a) Of the above claim(s) is/are wit 5) Claim(s) is/are allowed. 6) Claim(s) 21-35 and 38-41 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction are subject to restriction are subjected to by the Example Claim(s) is/are: Application Papers 9) The specification is objected to by the Example Claim(s) is/are: a) Applicant may not request that any objection is	thdrawn from consideration. and/or election requirement. aminer. accepted or b) objected to	·	
Replacement drawing sheet(s) including the country. The oath or declaration is objected to by the country of t	orrection is required if the drawin	g(s) is objected to. See 37 CFR 1.	` '
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for for a) All b) Some * c) None of: 1. Certified copies of the priority docu 2. Certified copies of the priority docu 3. Copies of the certified copies of the application from the International B * See the attached detailed Office action for	ments have been received. ments have been received in e priority documents have bee sureau (PCT Rule 17.2(a)).	Application No n received in this National Stag	j e
Attachment(s) 1) Notice of References Cited (PTO-892)	4\ ☐ Interview	Summary (PTO-413)	
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-94) Information Disclosure Statement(s) (PTO-1449 or PTO/92) Paper No(s)/Mail Date 	8) Paper No	(s)/Mail Date Informal Patent Application (PTO-152)	,

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

- 2. Claims 29, 30, 31, 33, and 34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itsudo et al (JP05-198512) in view of Hsieh; Chung-Ju et al. (US 6860138 B1). Itsudo teaches:
 - i. A wafer (2; Figure 6) processing apparatus (Figure 6, 8; abstract), comprising: a processing chamber (1; Figure 6; abstract) defined by a lower wall, an upper wall (8; Figure 6) and side walls extending from the lower wall to the upper wall (8; Figure 6), a wafer (2; Figure 6) supply opening (not shown; inherent) being formed in one of the walls for transferring a wafer (2; Figure 6) into the chamber (1; Figure 6; abstract); a susceptor (6; Figure 1) in the chamber (1; Figure 6; abstract) on which the wafer (2; Figure 6) can be located so that an upper surface of the wafer (2; Figure 6) faces the upper wall (8; Figure 6); a manifold (9; Figure 6) component located on the chamber (1; Figure 6; abstract) and, together with the upper surface of the upper wall (8; Figure 6), defining a manifold cavity (9; Figure 6); an exhaust line (4; Figure 6) connected to the chamber (1; Figure 6; abstract), for flowing a gas from the chamber (1; Figure 6; abstract), connected such that the gas has a tendency to flow toward the exhaust line (4; Figure 6); and a gas supply line (12; Figure 6) connected to the manifold (9; Figure 6) component, wherein the upper wall (8; Figure 6) has a plurality of gas supply openings (10; Figure 6, 8), each of the gas supply openings (10; Figure 6, 8) formed into an upper

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surface and out of a lower surface of the upper wall (8; Figure 6) such that each gas supply opening is defined by a corresponding interior surface of the upper wall (8; Figure 6), the gas supply openings (10; Figure 6, 8) being nonuniformly (Figure 8) distributed over the upper wall (8; Figure 6) to create a flow pattern that counteracts the tendency of the gas to flow toward the exhaust line (4; Figure 6), and thus promotes even processing over the upper surface of the wafer (2; Figure 6), as claimed by claim 29 – When the structure recited in the reference is substantially identical to that of the claims, claimed properties or functions are presumed to be inherent (In re Best, 562 F.2d 1252, 1255, 195 USPQ 430, 433 (CCPA 1977); MPEP 2112.01).

- ii. The apparatus (Figure 6, 8; abstract) of claim 29 wherein the openings (10; Figure 6, 8) are more densely located on one side of the upper wall (8; Figure 6) than on another side thereof, as claimed by claim 30
- iii. The apparatus (Figure 6, 8; abstract) of claim 30 wherein the openings (10; Figure 6, 8) are substantially equal in size, as claimed by claim 31
- iv. The apparatus (Figure 6, 8; abstract) of claim 29 wherein the exhaust line (4; Figure 6) is connected at an exhaust location which is off-center with respect to a center point (geometric center of 8; Figure 8) of the wafer (2; Figure 6), when viewed from above, so that the gas exits out of the chamber (1; Figure 6; abstract) at the exhaust location which is off-center with respect to a center point (geometric center of 8; Figure 8) of the wafer (2; Figure 6), as claimed by claim 33
- v. The apparatus (Figure 6, 8; abstract) of claim 33 wherein a channel (present, not labelled; Figure 1) is defined within the chamber (1; Figure 6; abstract), the channel (present, not

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labelled; Figure 1) being concentric with the wafer (2; Figure 6), gas flowing radially outwardly over the wafer (2; Figure 6) into the channel (present, not labelled; Figure 1), from the channel (present, not labelled; Figure 1), to the exhaust location into the exhaust line (4; Figure 6), as claimed by claim 34 – When the structure recited in the reference is substantially identical to that of the claims, claimed properties or functions are presumed to be inherent (In re Best, 562 F.2d 1252, 1255, 195 USPQ 430, 433 (CCPA 1977); MPEP 2112.01).

Itsudo does not teach a gas supply connected via a gas supply line opening formed through an upper surface of the manifold cavity.

Hsieh teaches a gas supply (70, 10a. etc..; Figure 1) connected via a gas supply line opening formed through an upper surface (80) of a manifold cavity (50).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to add Hsieh's gas supplies and for Itsudo to optimize the relative location of his gas supply line opening.

Motivation to add Hsieh's gas supplies and for Itsudo to optimize the relative location of his gas supply line opening is to use process gas sources as precursors for operations and to optimize desired process gas flows as taught by Itsudo (abstract). It is well established that the rearrangement of parts is considered obvious to those of ordinary skill (In re Japikse, 181 F.2d 1019, 86 USPQ 70 (CCPA 1950); In re Kuhle, 526 F.2d 553, 188 USPQ 7 (CCPA 1975); Ex parte Chicago Rawhide Manufacturing Co., 223 USPQ 351, 353 (Bd. Pat. App. & Inter. 1984).; MPEP 2144.04)

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- Claims 32, 35, 38, 39, and 40 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itsudo et al (JP05-198512) and Hsieh; Chung-Ju et al. (US 6860138 B1) in view of Nguyen, Tue (US 6,444,039 B1). Itsudo and Hsieh are discussed above. Itsudo further teaches Itsudo's apparatus (Figure 6, 8; abstract) of claim 29 wherein Itsudo's exhaust line (4; Figure 6) is connected at an exhaust location which is off-center with respect to a center point of Itsudo's wafer (2; Figure 6), when viewed from above, so that Itsudo's gas exits out of Itsudo's wafer (2; Figure 6) at Itsudo's exhaust location which is off-center with respect to a center point of Itsudo's wafer (2; Figure 6), as claimed by claim 40. Itsudo further teaches Itsudo's apparatus (Figure 6, 8; abstract) of claim 40 wherein Itsudo's openings (10; Figure 6, 8) are formed to increase a flow rate of Itsudo's gas over Itsudo's wafer (2; Figure 6) farther from Itsudo's exhaust location, as claimed by claim 41 When the structure recited in the reference is substantially identical to that of the claims, claimed properties or functions are presumed to be inherent (In re Best, 562 F.2d 1252, 1255, 195 USPQ 430, 433 (CCPA 1977); MPEP 2112.01). Itsudo and Hsieh do not teach:
 - i. Itsudo's apparatus (Figure 6, 8; abstract) of claim 29 wherein flow of gas in Itsudo's chamber (1; Figure 6; abstract) is laminar, as claimed by claim 32
 - ii. Itsudo's apparatus (Figure 6, 8; abstract) of claim 34 wherein Itsudo's openings (10;
 Figure 6, 8) are more densely located farther from Itsudo's exhaust location, as claimed by claim 35
- iii. Itsudo's apparatus (Figure 6, 8; abstract) of claim 29 wherein there are first and second ones of Itsudo's openings (10; Figure 6, 8) on opposing sides of a point (geometric center of 8; Figure 8) on Itsudo's upper wall (8; Figure 6), Itsudo's first opening having a lower

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end which is angularly displaced relative to an upper end thereof in a selected direction about Itsudo's point (geometric center of 8; Figure 8), and Itsudo's second opening having a lower end which is angularly displaced relative to an upper end thereof in Itsudo's selected direction, so that Itsudo's openings (10; Figure 6, 8) jointly create a circular gas flow pattern in Itsudo's chamber (1; Figure 6; abstract), as claimed by claim

38 – Applicant's Figure 4, 5 embodiment

iv. Itsudo's apparatus (Figure 6, 8; abstract) of claim 38 wherein a third of Itsudo's openings (10; Figure 6, 8), on a side of Itsudo's second opening opposing Itsudo's first opening, has a lower end which is displaced in Itsudo's first direction relative to an upper end thereof, as claimed by claim 39

Nguyen teaches a portion (vertical part) of a gas distribution plate (111; Figure 10) including injection holes (117, Figure 10) with Applicant's claimed angular displacement as per Applicant's Figures 4, 5.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to angle Itsudo's gas supply openings (10; Figure 6, 8) as taught by Nguyen, further to process the wafer under laminar flow including optimized hole distributions as taught by Itsudo.

Motivation to angle Itsudo's gas supply openings (10; Figure 6, 8) as taught by Nguyen, further to process the wafer under laminar flow including optimized hole distributions as taught by Itsudo is for influencing flow patterns of Itsudo's process gases to achieve controlled CVD film thickness distributions as taught by Itsudo (abstract).

Response to Arguments

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4. Applicant's arguments with respect to claims 29-35, and 38-41 have been considered but are most in view of the new grounds of rejection.

Conclusion

5. Applicant's amendment necessitated the new grounds of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Examiner Rudy Zervigon whose telephone number is (571) 272.1442. The examiner can normally be reached on a Monday through Thursday schedule from 8am through 7pm. The official fax phone number for the 1763 art unit is (703) 872-9306. Any Inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Chemical and Materials Engineering art unit receptionist at (571) 272-1700. If the

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examiner can not be reached please contact the examiner's supervisor, Parviz Hassanzadeh, at

(571) 272-1435.

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